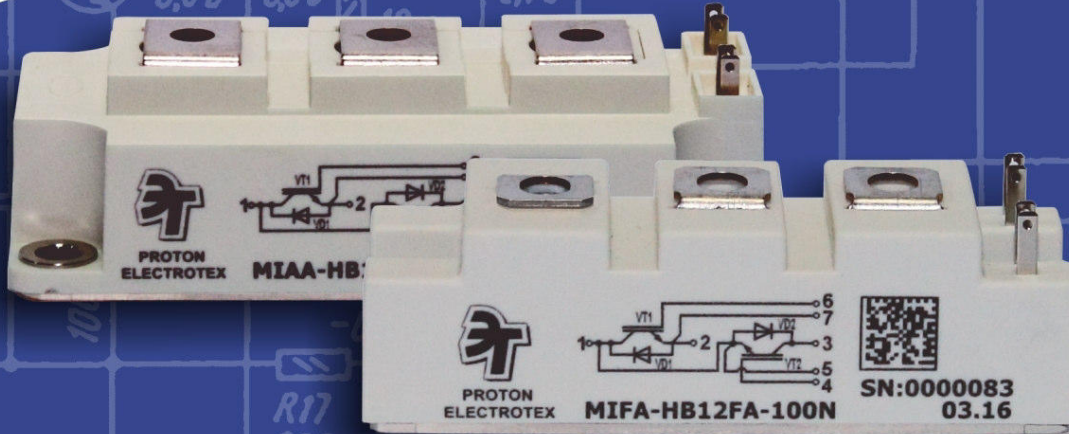




**PROTON-ELECTROTEX**  
POWER SEMICONDUCTOR DEVICES

# MEDIUM POWER IGBT MODULES



Circuit Diagram:

- HB – half bridge
- HC – high side chopper
- LC – low side chopper
- CE – common emitter

- Standard housing with 62 mm and 34 mm baseplate width
- DCB isolated copper baseplate
- Low static and dynamic losses
- Ultrasonically welded power terminals

## Basic characteristics

Part number	$V_{CES}$ , V	Baseplate width, mm	Nominal current (IGBT/diode), A	$V_{CEsat}$ , V typ., @Tc=25°C
MIAA-xx12FA-200N	1200	62	200	1,8
MIAA-xx12FA-300N	1200	62	300	1,8
MIAA-xx12FA-400N	1200	62	400	1,8
MIFA-xx12FA-100N	1200	34	100	1,8
MIFA-xx12FA-150N	1200	34	150	1,8
MIFA-xx12FA-200N	1200	34	200	1,8
MIAA-xx17FA-150N	1700	62	150	1,9
MIAA-xx17FA-200N	1700	62	200	1,9
MIAA-xx17FA-300N	1700	62	300	1,9
MIFA-xx17FA-075N	1700	34	75	1,9
MIFA-xx17FA-100N	1700	34	100	1,9
MIFA-xx17FA-150N	1700	34	150	1,9

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